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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	369-LFBGA
Supplier Device Package	369-PBGA (19x19)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8306scvmafdca

  - The power management controller detects that the system is not idle and there are outstanding transactions on the internal bus or an external interrupt.
- Parallel I/O
  - General-purpose I/O (GPIO)
    - 56 parallel I/O pins multiplexed on various chip interfaces
    - Interrupt capability
- System timers
  - Periodic interrupt timer
  - Software watchdog timer
  - Eight general-purpose timers
- Real time clock (RTC) module
  - Maintains a one-second count, unique over a period of thousands of years
  - Two possible clock sources:
    - External RTC clock (RTC_PIT_CLK)
    - CSB bus clock
- IEEE Std. 1149.1™ compliant JTAG boundary scan

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8306S. The MPC8306S is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic	Symbol	Max Value	Unit	Notes
Core supply voltage	V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	–0.3 to 1.26	V	—
DDR2 DRAM I/O voltage	GV_{DD}	–0.3 to 1.98	V	—
Local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, USB and JTAG I/O voltage	OV_{DD}	–0.3 to 3.6	V	2

Table 1. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Max Value	Unit	Notes
Input voltage	DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	3
	DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	3
	Local bus, DUART, SYS_CLK_IN, system control and power management, I^2C, SPI, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. OVDD here refers to NVDDA, NVDDB, NVDDC, NVDDF, NVDDG, and NVDDH from the ball map.
3. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
4. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.

2.1.2 Power Supply Voltage Specification

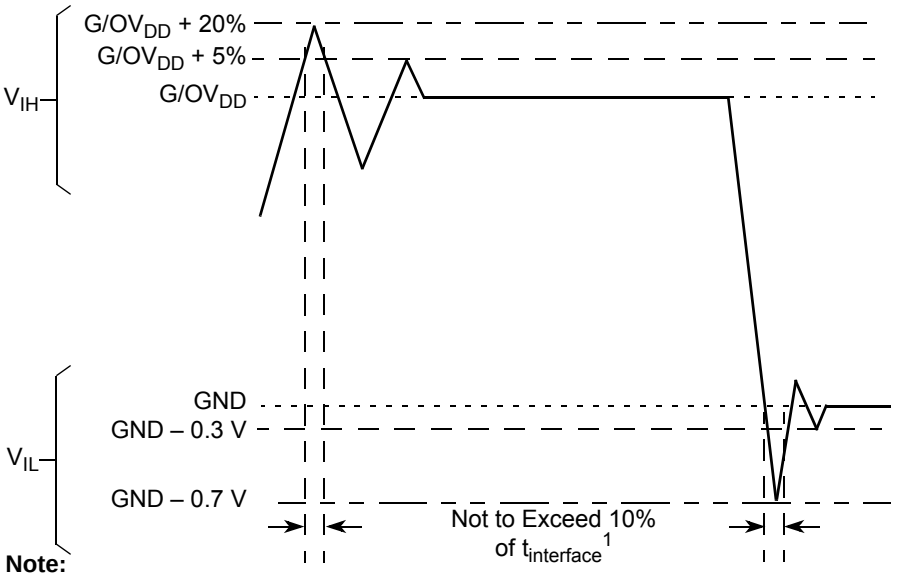
The following table provides the recommended operating conditions for the MPC8306S. Note that these values are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Note
Core supply voltage	V_{DD}	1.0 V ± 50 mV	V	1
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	1.0 V ± 50 mV	V	1
DDR2 DRAM I/O voltage	GV_{DD}	1.8 V ± 100 mV	V	1
Local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, USB and JTAG I/O voltage	OV_{DD}	3.3 V ± 300 mV	V	1, 3
Junction temperature	T_A/T_J	0 to 105	°C	2

Notes:
1. GV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. Minimum temperature is specified with T_A(Ambient Temperature); maximum temperature is specified with T_J(Junction Temperature).
3. OVDD here refers to NVDDA, NVDDB, NVDDC, NVDDF, NVDDG, and NVDDH from the ball map.

The following figure shows the undershoot and overshoot voltages at the interfaces of the MPC8306S



Note:
1. $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/OV_{DD}

4.2 AC Electrical Characteristics

The primary clock source for the MPC8306S is SYS_CLK_IN. The following table provides the clock input (SYS_CLK_IN) AC timing specifications for the MPC8306S. These specifications are also applicable for QE_CLK_IN.

Table 8. SYS_CLK_IN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Note
SYS_CLK_IN frequency	$f_{SYS\_CLK\_IN}$	24	—	66.67	MHz	1
SYS_CLK_IN cycle time	$t_{SYS\_CLK\_IN}$	15	—	41.6	ns	—
SYS_CLK_IN rise and fall time	t_{KH}, t_{KL}	1.1	—	2.8	ns	2
SYS_CLK_IN duty cycle	$t_{KHK}/t_{SYS\_CLK\_IN}$	40	—	60	%	3
SYS_CLK_IN jitter	—	—	—	±150	ps	4, 5

Notes:
1. **Caution:** The system, core and QUICC Engine block must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for SYS_CLK_IN are measured at 0.33 and 2.97 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The SYS_CLK_IN driver's closed loop jitter bandwidth should be < 500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYS_CLK_IN drivers with the specified jitter.
6. Spread spectrum is allowed up to 1% down-spread @ 33kHz (max rate).

5 RESET Initialization

This section describes the AC electrical specifications for the reset initialization timing requirements of the MPC8306S. The following table provides the reset initialization AC timing specifications for the reset component(s).

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Note
Required assertion time of $\overline{\text{HRESET}}$ to activate reset flow	32	—	$t_{SYS\_CLK\_IN}$	1
Required assertion time of PORESET with stable clock applied to SYS_CLK_IN	32	—	$t_{SYS\_CLK\_IN}$	1
$\overline{\text{HRESET}}$ assertion (output)	512	—	$t_{SYS\_CLK\_IN}$	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:3]) with respect to negation of $\overline{\text{PORESET}}$	4	—	$t_{SYS\_CLK\_IN}$	1, 2
Input hold time for POR config signals with respect to negation of $\overline{\text{HRESET}}$	0	—	ns	1, 2

Notes:
1. $t_{SYS\_CLK\_IN}$ is the clock period of the input clock applied to SYS_CLK_IN. For more details, see the *MPC8306S PowerQUICC II Pro Integrated Communications Processor Family Reference Manual*.
2. POR configuration signals consist of CFG_RESET_SOURCE[0:3].

The following table provides the PLL lock times.

Table 10. PLL Lock Times

Parameter/Condition	Min	Max	Unit	Note
PLL lock times	—	100	μs	—

5.1 Reset Signals DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S reset signals mentioned in Table 9.

Table 11. Reset Signals DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Note
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	1
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±5	μA	—

Note:
1. This specification applies when operating from 3.3 V supply.

6 DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR2 SDRAM interface of the MPC8306S. Note that DDR2 SDRAM is GV_{DD}(typ) = 1.8 V.

6.1 DDR2 SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8306S when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Note
I/O supply voltage	GV_{DD}	1.7	1.9	V	1
I/O reference voltage	MVREF	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MVREF – 0.04	MVREF + 0.04	V	3
Input high voltage	V_{IH}	MVREF+ 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MVREF – 0.125	V	—
Output leakage current	I_{OZ}	–9.9	9.9	μA	4

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Note
Output high current (V_{OUT} = 1.35 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MVREF is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MVREF may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREF. This rail should track variations in the DC level of MVREF.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

The following table provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.100 V, f = 1 MHz, T_A = 25 °C, V_{OUT} = GV_{DD} ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR2 SDRAM interface.

6.2.1 DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM (GV_{DD}(typ) = 1.8 V).

Table 14. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 V± 100mV.

Parameter	Symbol	Min	Max	Unit	Note
AC input low voltage	V_{IL}	—	MVREF – 0.25	V	—
AC input high voltage	V_{IH}	MVREF + 0.25	—	V	—

The following table provides the input AC timing specifications for the DDR2 SDRAM interface.

Table 15. DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8V ± 100mV.

Parameter	Symbol	Min	Max	Unit	Note
Controller skew for MDQS—MDQ/MDM	t_{CISKEW}			ps	1, 2

The following figure shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

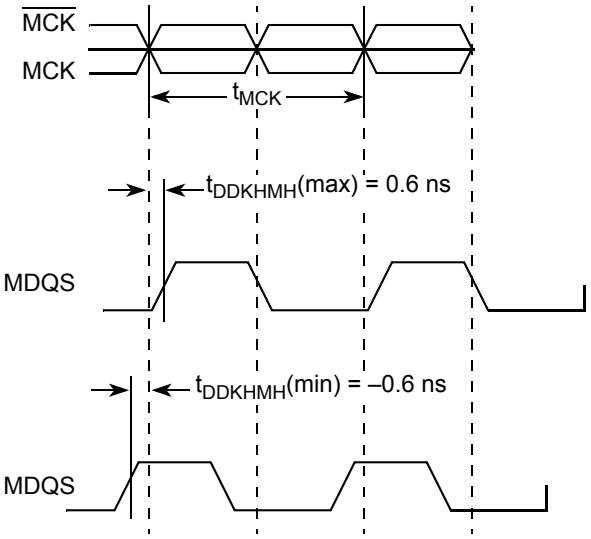


Figure 5. Timing Diagram for t_{DDKHMH}

The following figure shows the DDR2 SDRAM output timing diagram.

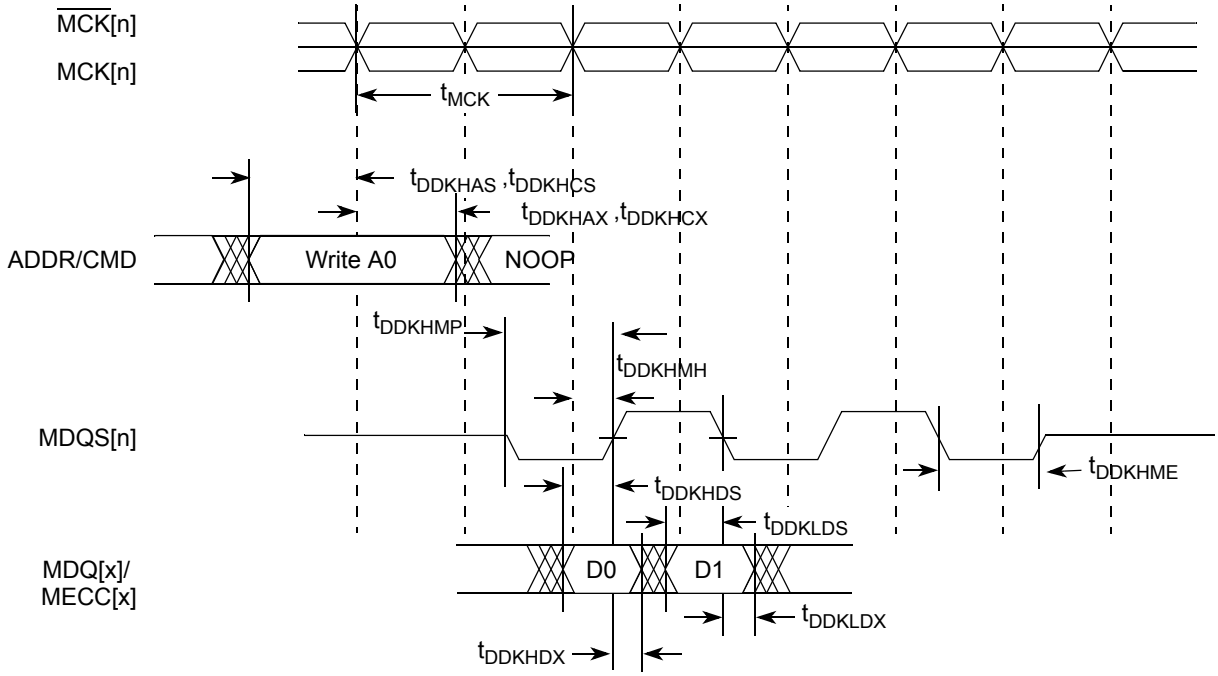


Figure 6. DDR2 SDRAM Output Timing Diagram

Table 19. MII and RMII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	OV_{DD}	—		3	3.6	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	OV_{DD} = Min	2.40	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±5	μA

8.2 MII and RMII AC Timing Specifications

The AC timing specifications for MII and RMII are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

The following table provides the MII transmit AC timing specifications.

Table 20. MII Transmit AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise V_{IL}(min) to V_{IH}(max)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall V_{IH}(max) to V_{IL}(min)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Table 25. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Note
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	—
MDIO to MDC setup time	t_{MDDVKH}	8.5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

The following figure shows the MII management AC timing diagram.

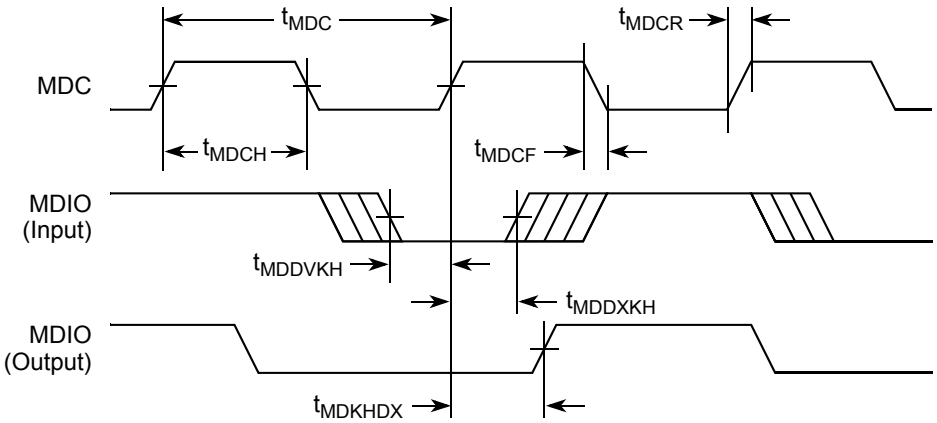
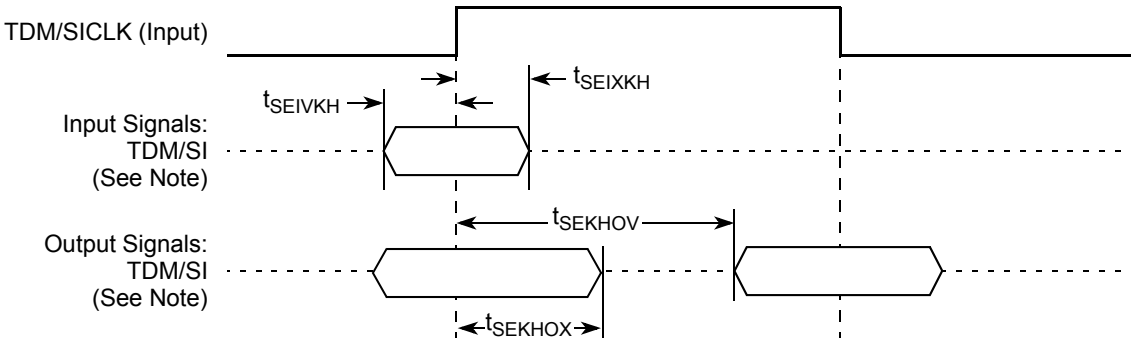


Figure 17. MII Management Interface Timing Diagram

The following figure represents the AC timing from Table 27. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.



Note: The clock edge is selectable on TDM/SI.

Figure 19. TDM/SI AC Timing (External Clock) Diagram

10 HDLC

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), of the MPC8306S.

10.1 HDLC DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S HDLC protocol.

Table 28. HDLC DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

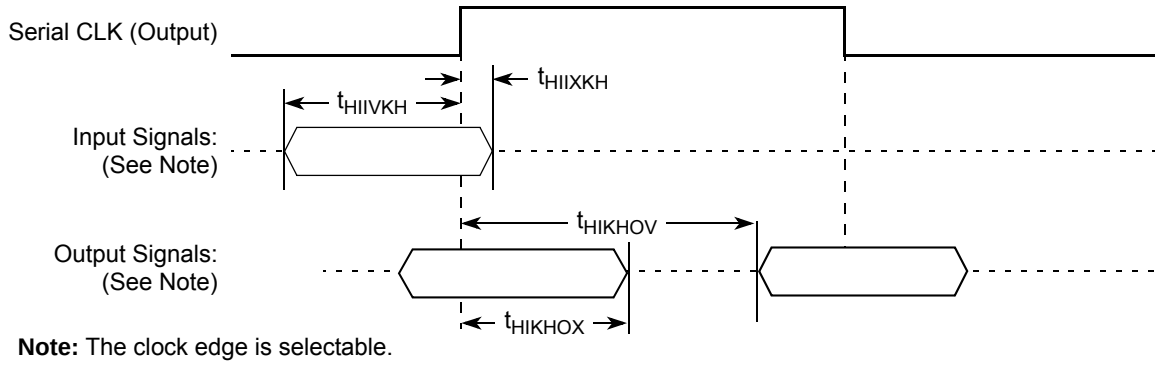
10.2 HDLC AC Timing Specifications

The following table provides the input and output AC timing specifications for HDLC protocol.

Table 29. HDLC AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	t_{HIKHOV}	0	9	ns
Outputs—External clock delay	t_{HEKHOV}	1	12	ns
Outputs—Internal clock high impedance	t_{HIKHOX}	0	5.5	ns

The following figure shows the timing with internal clock.



Note: The clock edge is selectable.

Figure 22. AC Timing (Internal Clock) Diagram

11 USB

11.1 USB Controller

This section provides the AC and DC electrical specifications for the USB (ULPI) interface.

11.1.1 USB DC Electrical Characteristics

The following table provides the DC electrical characteristics for the USB interface.

Table 30. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2.0	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

11.1.2 USB AC Electrical Specifications

The following table describes the general timing parameters of the USB interface.

Table 31. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Note
USB clock cycle time	t_{USCK}	15	—	ns	—
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	—
input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	—
USB clock to output valid—all outputs (except USBDR_STP_USBDR_STP)	t_{USKHOV}	—	7	ns	—

12 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8306S.

12.1 DUART DC Electrical Characteristics

The following table provides the DC electrical characteristics for the DUART interface of the MPC8306S.

Table 32. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage OV_{DD}	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V
Input current (0 V ≤ V_{IN} ≤ OV_{DD})[1]	I_{IN}	—	±5	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

12.2 DUART AC Electrical Specifications

The following table provides the AC timing parameters for the DUART interface of the MPC8306S.

Table 33. DUART AC Timing Specifications

Parameter	Value	Unit	Note
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate is limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

Table 42. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

17.2 SPI AC Timing Specifications

The following table and provide the SPI input and output AC timing specifications.

Table 43. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of SPICLK to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).
3. All units of output delay must be enabled for 8306S output port spimosi (SPI Master Mode)
4. delay units must not be enabled for Slave Mode.

The following figure provides the AC test load for the SPI.

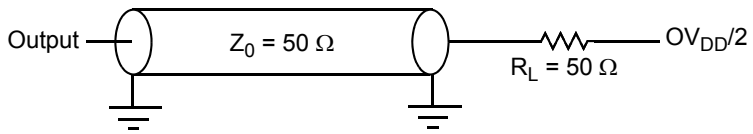


Figure 29. SPI AC Test Load

Figure 30 and Figure 31 represent the AC timing from Table 43. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

19.3 Pinout Listings

Following table shows the pin list of the MPC8306S.

Table 46. MPC8306S Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR Memory Controller Interface				
MEMC_MDQ[0]	W5	IO	GV_{DD}	—
MEMC_MDQ[1]	V4	IO	GV_{DD}	—
MEMC_MDQ[2]	Y4	IO	GV_{DD}	—
MEMC_MDQ[3]	AB1	IO	GV_{DD}	—
MEMC_MDQ[4]	AA1	IO	GV_{DD}	—
MEMC_MDQ[5]	Y2	IO	GV_{DD}	—
MEMC_MDQ[6]	Y1	IO	GV_{DD}	—
MEMC_MDQ[7]	W2	IO	GV_{DD}	—
MEMC_MDQ[8]	G2	IO	GV_{DD}	—
MEMC_MDQ[9]	G1	IO	GV_{DD}	—
MEMC_MDQ[10]	F1	IO	GV_{DD}	—
MEMC_MDQ[11]	E2	IO	GV_{DD}	—
MEMC_MDQ[12]	E1	IO	GV_{DD}	—
MEMC_MDQ[13]	E4	IO	GV_{DD}	—
MEMC_MDQ[14]	F4	IO	GV_{DD}	—
MEMC_MDQ[15]	D1	IO	GV_{DD}	—
MEMC_MDM[0]	AB2	O	GV_{DD}	—
MEMC_MDM[1]	G4	O	GV_{DD}	—
MEMC_MDQS[0]	V5	IO	GV_{DD}	—
MEMC_MDQS[1]	F5	IO	GV_{DD}	—
MEMC_MBA[0]	L2	O	GV_{DD}	—
MEMC_MBA[1]	L1	O	GV_{DD}	—
MEMC_MBA[2]	R4	O	GV_{DD}	—
MEMC_MA[0]	M1	O	GV_{DD}	—
MEMC_MA[1]	M4	O	GV_{DD}	—
MEMC_MA[2]	N1	O	GV_{DD}	—
MEMC_MA[3]	N2	O	GV_{DD}	—
MEMC_MA[4]	P1	O	GV_{DD}	—
MEMC_MA[5]	N4	O	GV_{DD}	—
MEMC_MA[6]	P2	O	GV_{DD}	—
MEMC_MA[7]	R1	O	GV_{DD}	—

20 Clocking

The following figure Figure 39 shows the internal distribution of clocks within the MPC8306S.

Figure 38. MPC8306S Clock Subsystem

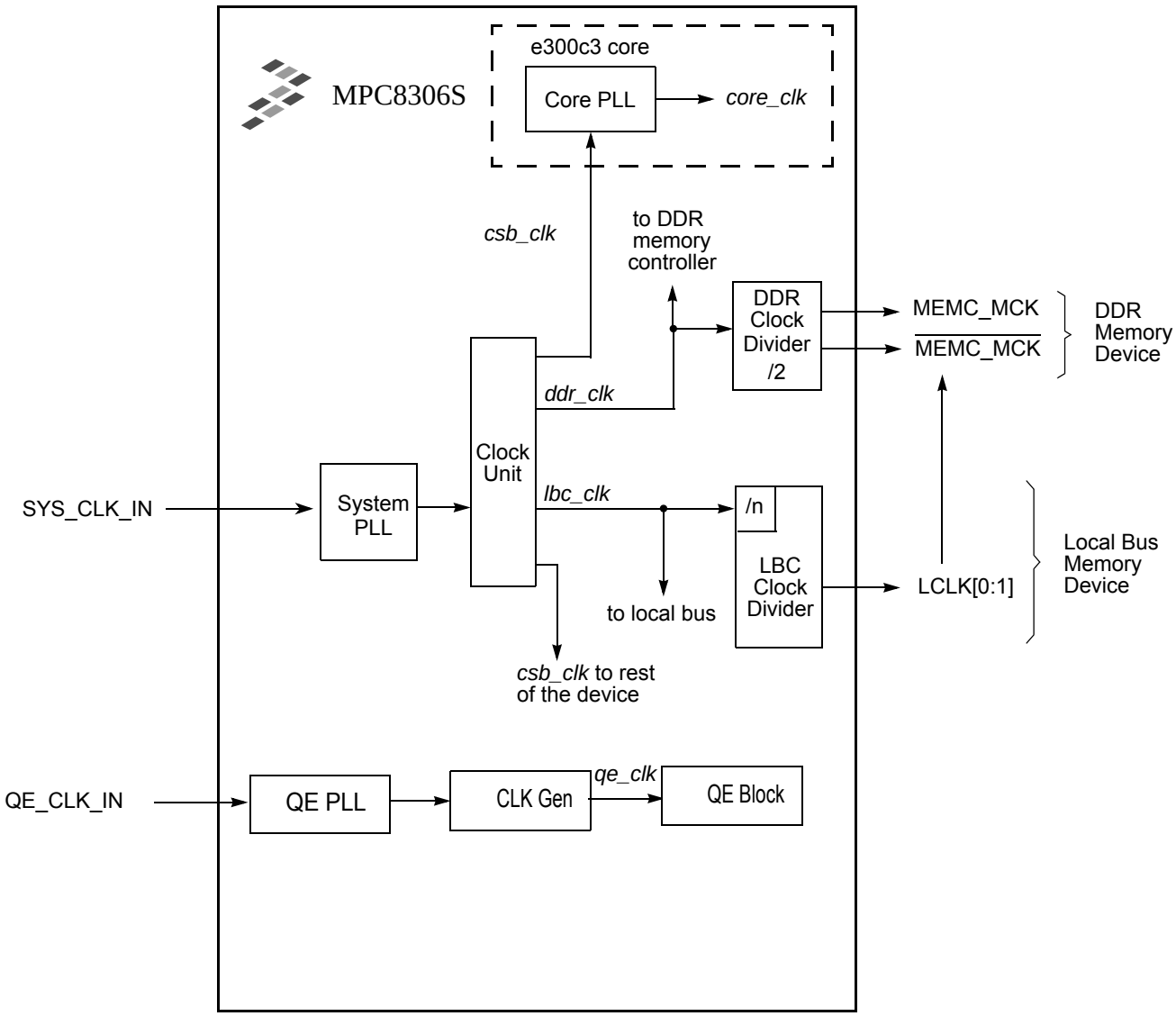


Figure 39. MPC8306S Clock Subsystem

The primary clock source for MPC8306S is SYS_CLK_IN.

Figure 40.

In addition, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. These units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset.

The following table specifies which units have a configurable clock frequency. For detailed description, refer to the "System Clock Control Register (SCCR)" section in the *MPC8306S PowerQUICC II Pro Integrated Communications Processor Family Reference Manual*.

Table 47. Configurable Clock Units

Unit	Default Frequency	Options
I2C,SDHC, USB, DMA Complex	*csb_clk*	Off, csb_clk, *csb_clk*/2, *csb_clk*/3

NOTE

Setting the clock ratio of these units must be performed prior to any access to them.

The following table provides the maximum operating frequencies for the MPC8306S MAPBGA under recommended operating conditions (see Table 2).

Table 48. Operating Frequencies for MAPBGA

Characteristic[1]	Max Operating Frequency	Unit
e300 core frequency (*core_clk*)	266	MHz
Coherent system bus frequency (*csb_clk*)	133	MHz
QUICC Engine frequency (*qe_clk*)	233	MHz
DDR2 memory bus frequency (MCLK)[2]	167	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz

Notes:
1. The SYS_CLK_IN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting csb_clk, MCLK, LCLK, and core_clk frequencies do not exceed their respective maximum or minimum operating frequencies.
2. The DDR2 data rate is 2× the DDR2 memory bus frequency.
3. The local bus frequency is 1/2, 1/4, or 1/8 of the lb_clk frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the csb_clk frequency (depending on RCWL[LBCM]).

20.2 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 49 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO divider). The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz.

As described in Section 20, "Clocking," the LBCM, DDRCM, and SPMF parameters in the reset configuration word low select the ratio between the primary clock input (*SYS_CLK_IN)* and the internal

Table 51. e300 Core PLL Configuration (continued)

RCWL[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider
0-1	2-5	6		
00	0001	1	1.5:1	÷ 2
01	0001	1	1.5:1	÷ 4
10	0001	1	1.5:1	÷ 8
11	0001	1	1.5:1	÷ 8
00	0010	0	2:1	÷ 2
01	0010	0	2:1	÷ 4
10	0010	0	2:1	÷ 8
11	0010	0	2:1	÷ 8
00	0010	1	2.5:1	÷ 2
01	0010	1	2.5:1	÷ 4
10	0010	1	2.5:1	÷ 8
11	0010	1	2.5:1	÷ 8
00	0011	0	3:1	÷ 2
01	0011	0	3:1	÷ 4
10	0011	0	3:1	÷ 8
11	0011	0	3:1	÷ 8

NOTE

Core VCO frequency = core frequency × VCO divider. The VCO divider (RCWL[COREPLL[0:1]]), must be set properly so that the core VCO frequency is in the range of 400–800 MHz.

20.4 QUICC Engine PLL Configuration

The QUICC Engine PLL is controlled by the RCWL[CEPMF] and RCWL[CEPDF] parameters. The following table shows the multiplication factor encodings for the QUICC Engine PLL.

Table 52. QUICC Engine PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
00000–00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6

to minimize inductance. Suggested bulk capacitors—100 to 330 µF (AVX TPS tantalum or Sanyo OSCON).

22.4 Output Buffer DC Impedance

For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 42). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

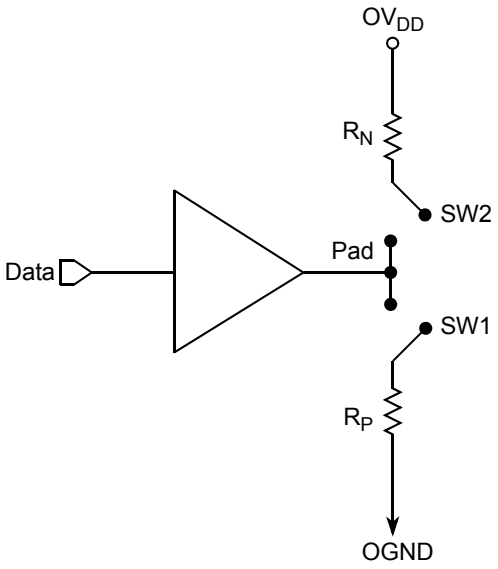


Figure 42. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

The following table summarizes the signal impedance targets. The driver impedance is targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 56. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration and Power Management	DDR DRAM	Symbol	Unit
R_N	42 Target	20 Target	Z_0	Ω
R_P	42 Target	20 Target	Z_0	Ω
Differential	NA	NA	Z_{DIFF}	Ω

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

22.5 Configuration Pin Multiplexing

The MPC8306S provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (Refer to the "Reset, Clocking and Initialization" of *MPC8306S PowerQUICC II Pro Integrated Communications Processor Family Reference Manual*). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

23 Ordering Information

This section presents ordering information for the devices discussed in this document, and it shows an example of how the parts are marked. Ordering information for the devices fully covered by this document is provided in Section 23.1, "Part Numbers Fully Addressed by This Document."

23.1 Part Numbers Fully Addressed by This Document

The following table provides the Freescale part numbering nomenclature for the MPC8306S family. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the maximum processor core frequency, the part numbering scheme also includes the maximum effective DDR memory speed and QUICC Engine bus frequency. Each part number also contains a revision code which refers to the die mask revision number.

How to Reach Us:

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USA/Europe or Locations Not Listed:
Freescale Semiconductor, Inc.
Technical Information Center, EL516
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Tempe, Arizona 85284
1-800-521-6274 or
+1-480-768-2130
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Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
www.freescale.com/support

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku
Tokyo 153-0064
Japan
0120 191014 or
+81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
support.asia@freescale.com

For Literature Requests Only:
Freescale Semiconductor
Literature Distribution Center
1-800 441-2447 or
+1-303-675-2140
Fax: +1-303-675-2150
LDCForFreescaleSemiconductor
@hibbertgroup.com

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